

AS1345 18V, High Efficiency, DC-DC Step-Up Converter

General Description

The AS1345 high efficiency DC-DC step-up converter contains an internal N-channel and an internal P-channel output isolation switch.

The device operates from a 2.9V to 5.0V supply and can boost voltages up to 18V.

A hysteretic control scheme is used to provide the highest operating efficiency over a wide range of input and output load conditions. The internal MOSFET switches reduce the external component count and a high switching frequency allows the use of tiny surface mount components.

The AS1345 employ a factory set current limit to reduce ripple and external component size in low output current applications. With a 500mA current limit the AS1345 is capable of providing 20mA @ 18V output.

Figure AS1345 – 1: Available Products

Devices	Peak Coil Current	Output
AS1345A	100mA	adjustable or fixed
AS1345B	200mA	adjustable or fixed
AS1345C	350mA	adjustable or fixed
AS1345D	500mA	adjustable or fixed

For order related information, please refer to "Ordering Information" on page 24.

Built-in safety features protect the internal switches and output components from fault conditions. Additional power-saving attributes include a very low quiescent current and a true shutdown mode.

Figure AS1345 – 2: Key Benefits and Features

Benefits	Features
Supports Lithium primary and re-chargeable batteries	Input Voltage Range: 2.9V to 5.0V
Supports a variety of end applications	Adjustable Output Voltage Range: 5.0V to 18V

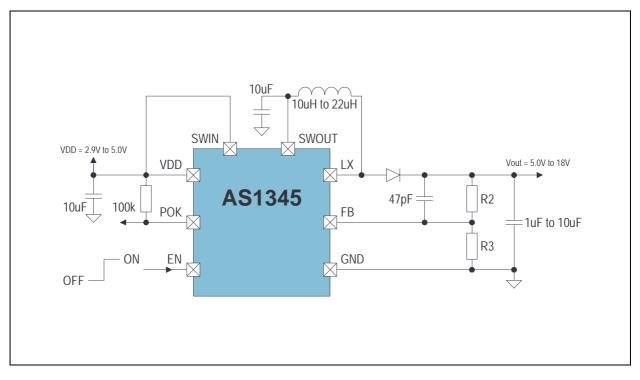


Benefits	Features
Supports a variety of end applications	Output Current up to 40mA
Allows optimization of circuit depending on output power demands	Inductor Peak Currents: 100, 200, 350 and 500 mA
Battery life improved	90% Efficiency
Battery supply isolated during shutdown	True Shutdown
Fault tolerant	Short Circuit and Thermal Protection
Small chipscale package	Packages: • 8-pin (2x2mm) TDFN • 8-bumps (1.570mm x 0.895mm) WL-CSP with 0.4mm pitch

Applications

The AS1345 is ideal for small and low current demand LCD panels, as well as for polymer LEDs (OLED), cell phones, PDAs, readers, mobile terminals and 3D shutter glasses.

Figure AS1345 – 3: Typical Application Diagram





Pin Assignments

Figure AS1345 – 4: Pin Assignments (Top View)

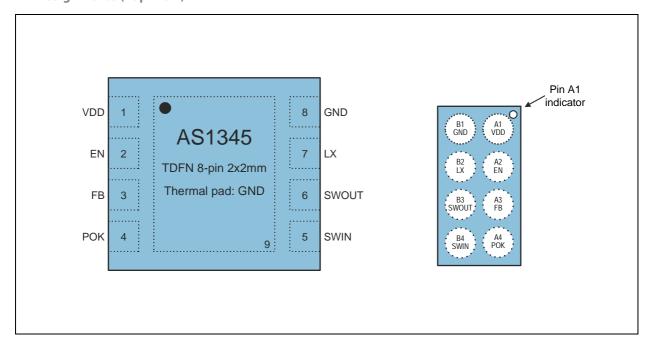


Figure AS1345 – 5: Pin Descriptions

Pin N	umber	Pin Name	Description
TDFN	WLP	Fin Name	Description
2	A2	EN	Enable Pin . Logic controlled shutdown input, 1.8V CMOS compatible; 1 = Normal operation 0 = Shutdown On request a 100k Ω pull-down resistor can be enabled (factory set).
8	B1	GND	Ground
7	B2	LX	Inductor. The drain of the internal N-channel MOSFET. Connect to power inductor and to anode of a schottky diode.
3	A3	FB	Feedback Pin . Feedback input to the gm error amplifier. For an adjustable output voltage connect a resistor divider to this pin. The output can be adjusted from 5.0V to 18V by: VOUT = VREF x (1 + R2/R3) If the fixed output voltage version is used, connect this pin to VOUT.
4	A4	РОК	POK . Open Drain Output. POK remains low while VOUT is less than 90% of nominal VOUT. Connect a 100k Ω pull-up resistor from this pin to VDD.



Pin Nu	umber	Pin Name	Description
TDFN	WLP		Description
6	B3	SWOUT	Shutdown Disconnect Switch Out . Output pin of the internal P-channel MOSFET. Connect to power inductor and decouple to GND with a 10μ F low ESR ceramic capacitor. When the input disconnect feature is not desired, SWOUT should be connected to SWIN and VDD.
5	B4	SWIN	Shutdown Disconnect Switch In. Input pin of the internal P-channel MOSFET.
1	A1	VDD	Supply Voltage. Connect to a 2.9V to 5.0V input supply. Bypass this pin with a $10\mu F$ capacitor.
9	-	NC	Exposed Pad . This pad is not connected internally. This pin also functions as a heat sink. Solder it to a large pad or to the circuit-board ground plane to maximize power dissipation.



Absolute Maximum Ratings

Stresses beyond those listed in the table below may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in "Electrical Characteristics" on page 6 is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

Figure AS1345 – 6: Absolute Maximum Ratings

Parameter		Min	Max	Unit	Comments
			Electrica	al Paramo	eters
VDD, SWIN, SWOU	JT to GND	-0.3	7	V	
LX, FB to G	ND	-0.3	20	V	
Input Current (I immunit		-100	100	mA	Norm: JEDEC 78
SWIN to SWOUT Cu	urrent Limit		1	А	
		J	Electrost	atic Disc	harge
Electrostatic Disch	narge HBM	±	:2	kV	Norm: MIL 883 E method 3015
	Temperature Range				prage Conditions
Junction temp	Junction temperature		+110	°C	
Storage tomporat	Storage temperature range		+125	°C	for WL-CSP
Storage temperat	ure range	-55	+150	°C	for TDFN
	WL-CSP		60		Junction-to-ambient thermal resistance is very
Package thermal data	TDFN		97	°C/W	dependent on application and board-layout. In situations where high maximum power dissipation exists, special attention must be paid to thermal dissipation during board design.
Package body	WL-CSP		+260	°C	Norm IPC/JEDEC J-STD-020
temperature	TDFN		+200		Norm IPC/JEDEC J-STD-020
Humidity non-co	Humidity non-condensing		85	%	
Moisture sensit			3		Represents a maximum floor life time of 168h for TDFN
MOISTURE SEIISIT		1			Represents a maximum floor life time of unlimited for WL-CSP

Note: The reflow peak soldering temperature (body temperature) specified is in accordance with IPC/JEDEC J-STD-020"Moisture/Reflow Sensitivity Classification for Non-Hermetic Solid State Surface Mount Devices".



Electrical Characteristics

All limits are guaranteed. The parameters with Min and Max values are guaranteed by production tests or SQC (Statistical Quality Control) methods.

VDD = VSHDNN = VSWIN = 3.7V, VOUT = 15V, CIN = COUT = 10 μ F, typical values @ TAMB = +25°C (unless otherwise specified). All limits are guaranteed.

Symbol	Parameter	Conditions	Min	Тур	Max	Units
Тамв	Operating temperature range		-40		+85	°C
τJ	Operating junction temperature range		-40		+110	°C
		Input				
Vdd	Supply voltage range	SWIN connected to VDD	2.9		5.0	V
	Minimum startup voltage	VDD = SWIN		2.7		V
VUVLO	VDD undervoltage lockout	VDD decreasing (50mV Hysteresis)		2.7		V
		Regulation		L	1	
νουτ	Adjustable output voltage range	External FB divider	5		18	V
	Feedback voltage tolerance	Tolerance of FB resistors not included	-3		+3	%
				12		
	Fixed output voltage	Internal FB divider		15		V
				17		
Vfb	Feedback voltage	For adjustable Vout only		1.25		V
	Feedback input current			10	1000	nA
	Line regulation	VDD = 3.5V to 3.7V		200		mV
	Load regulation	Vout = 15V, Iload = 0mA to 5mA		50		mV
η	Efficiency	L = 22µH, VDD = Vswin = 3.7V, Vout = 15V, Iload = 10mA		90		%
	•	Operating Current				·
	Shutdown current @ VDD	Vshdnn = 0V			1	
Ishdn	Shutdown current @ SWIN	ער אויטחנע – VV ער אויטחנע			1	μΑ
lq	Quiescent current	No switching, VFB = 1.5V		25		μΑ
Iddload	Load current	Vout = 15V, Iload = 5mA		25		mA



Symbol	Parameter	Conditions	Min	Тур	Max	Units
		AS1345A		100		mA
Ilimit	Coil peak current limit	AS1345B		200		mA
		AS1345C		350		mA
		AS1345D		500		mA
		Switches	1		L	L
R _{NMOS}	NMOS resistance			0.3		Ω
R _{PMOS}	PMOS resistance			0.15		Ω
		POK Output				
	POK output voltage 'low'	POK sinking 1mA		0.01	0.2	V
	POK output voltage 'high'	POK leakage 1µA	VDD		VDD - 0.1	v
	POK output high leakage current	POK = 3.7V			1	μΑ
	POK threshold	Rising edge, referenced to Vout(NOM)		90		%
		Shutdown		I	1	1
Vshdnh	SHDN input 'high'		1.26			V
Vshdnl	SHDN input 'low'	2.9V < VDD < 5.0V, no load			0.55	V
Ishdn	SHDN input current		-1		+1	μΑ
		Soft Start		I	I	I
IPRE	Pre-charge current			100		mA
		Thermal Shutdown		1	1	1
	Thermal shutdown			150		°C
	Thermal shutdown hysteresis			10		°C



Typical Operating Characteristics

VOUT = 15V

Figure AS1345 – 7: Efficiency vs. IOUT; VIN = 2.7V, ILIMIT = 100mA

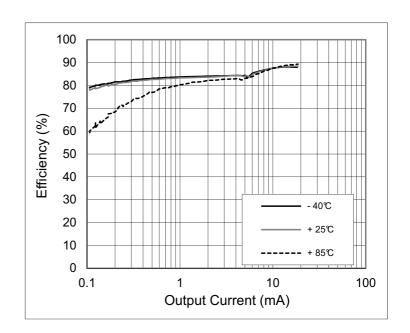


Figure AS1345 – 8: Efficiency vs. IOUT; VIN = 2.7V, ILIMIT = 500mA

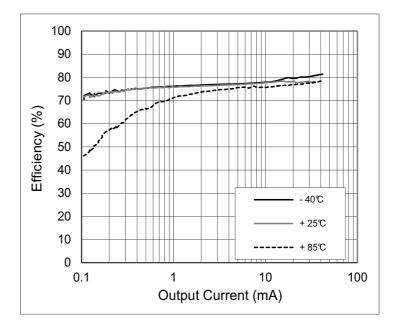




Figure AS1345 – 9: Efficiency vs. IOUT; VIN = 4.5V, ILIMIT = 100mA

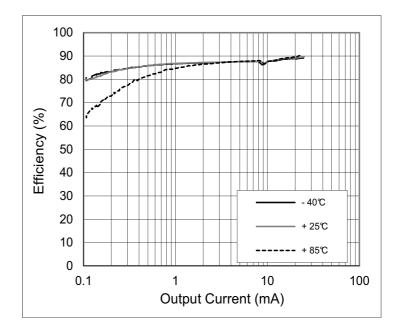


Figure AS1345 – 10: Efficiency vs. IOUT; VIN = 4.5V, ILIMIT = 500mA

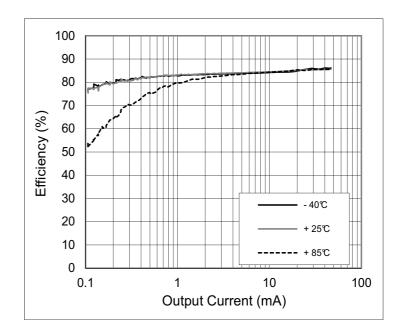




Figure AS1345 – 11: Efficiency vs. VIN; ILOAD = 5mA, ILIMIT = 100mA

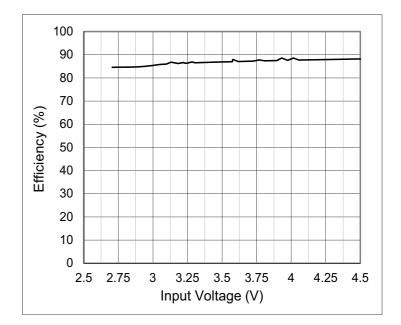


Figure AS1345 – 12: Efficiency vs. VIN; ILOAD = 5mA/20mA, ILIMIT = 500mA

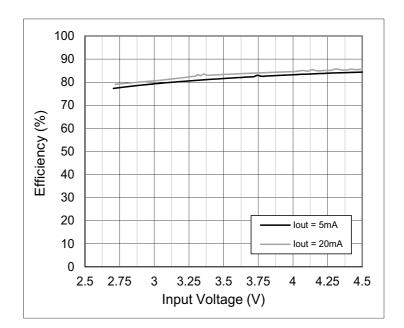




Figure AS1345 – 13: Vout vs. lout; VIN = 2.7V, ILIMIT = 100mA

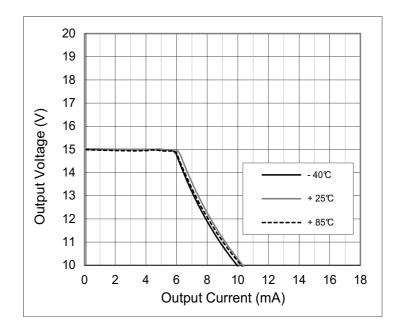


Figure AS1345 – 14: VOUT vs. IOUT; VIN = 4.5V, ILIMIT = 100mA

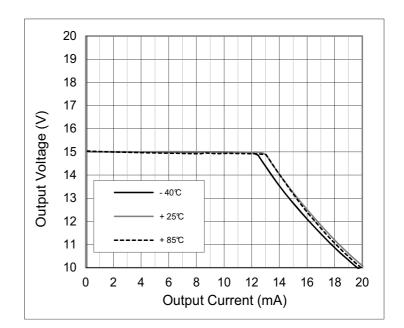
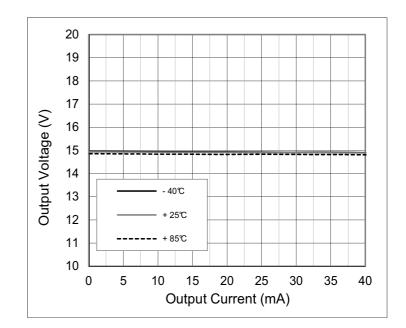




Figure AS1345 – 15: Vout vs. lout; VIN = 4.5V, ILIMIT = 500mA

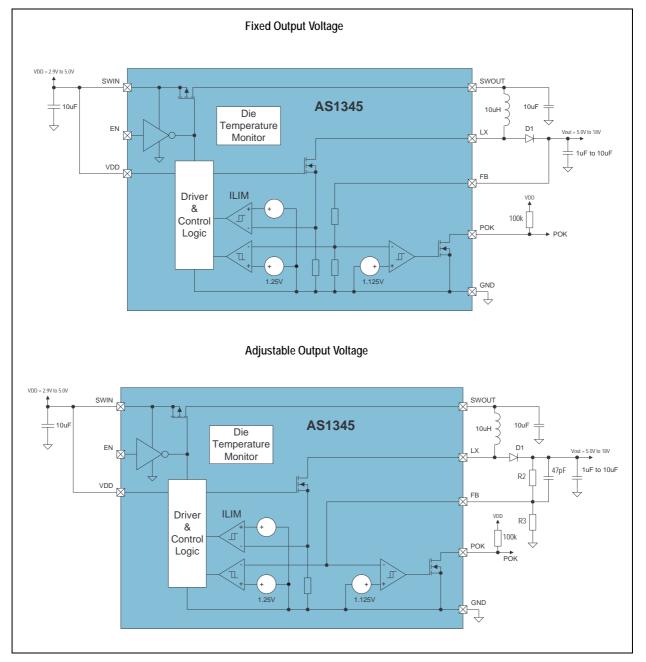




Detailed Description

The AS1345 is a compact step-up DC-DC converters that operates from a 2.9V to 5.0V supply. Consuming only 25µA of Quiescent current. These devices include an internal MOSFET switch with a low on-resistance. A true shutdown feature disconnects the battery from the load and reduces the supply current to 0.05µA (typ). These DC-DC converters are available with either a fixed output or are adjustable up to 18V. Four current-limit options are available: 100mA, 200mA, 350mA and 500mA.





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Modes of Operation

The AS1345 features an advanced current-limited control scheme operating in hysteretic mode. An internal P-channel MOSFET switch connects VDD to SWIN to provide power to the inductor when the converter is operating. When the converter is shut down, this switch disconnects the input supply from the inductor (see Figure 3). To boost the output voltage an N-channel MOSFET switch turns on and allows current to ramp up in the inductor. Once this current reaches the current limit, the switch turns off and the inductor current flows through D1 to supply the output. The switching frequency varies depending on the load and input voltage and can be up to 10kHz.

Shutdown

Drive EN low to enter shutdown mode. During shutdown the supply current drops to 0.05μ A (typ), the output is dis-connected from the input, and LX enters a high impedance state. The capacitance and load at the output set the rate at which VOUT decays. EN can be pulled as high as 6V regardless of the input and output voltages.

With a typical step-up converter circuit, the output remains connected to the input through the inductor and output rectifier, holding the output voltage to one diode drop below VDD when the converter is shutdown and allowing the output to draw power from the input.

The AS1345 features a True-Shutdown mode, disconnecting the output from the input with an internal P-channel MOSFET switch when shut down. This eliminates power draw from the input during shutdown mode.

Start-up and Inrush Limiting

If the ENABLE pin is high, the AS1345 uses a multi-stage start-up sequence. With increasing supply voltage, first the power-on circuitry becomes active and some internal blocks are initiated. If the supply exceeds the under-voltage-lockout threshold (2.7V typ), the pre-charge-phase is initiated. The capacitor at the SWOUT pin is charged to VIN, and the capacitor at VOUT is charged to VIN-VSD. During this phase the current is limited to 100mA typical. After the completion of the pre-charge-phase, the AS1345 enters into switching mode. Here the specified current-limit I_{PEAK} is used. The circuit operates at maximum frequency until the desired VOUT is reached. Then AS1345 switches to normal hysteretic operation mode.

If the load current is too high (>50mA) during the start-up-phase, the attainment of normal operation mode might be delayed or not done at all.



Adjustable Output Voltage

The output voltage of the AS1345 is adjustable from 5.0V to 18V by using a resistor voltage-divider (see Figure 17 and Figure 18). Select R1 from $10k\Omega$ to $600k\Omega$ and calculate R2 with the following equation:

(EQ 1)

 $VOUT = VREF (1 + R_2/R_3)$

Where: VREF = 1.25V

VOUT can range from 5.0V to 18V

For best accuracy, ensure that the bias current through the feedback resistors is at least $2\mu A$.

The AS1345 can also be used with a fixed output voltage. When using one of these parts, connect FB directly to the output (see Figure 19 and Figure 20).

For improved regulation speed and lower ripple C3 should be applied. For best ripple performance always the adjustable variant of the AS1345 together with C3 should be used. Other measures to reduce the ripple could be to select a low peak current I_{PEAK} and increase C4 and to decrease the value of L.

Figure AS1345 – 17: AS1345 with Adjustable Output Voltage, with Output Disconnect

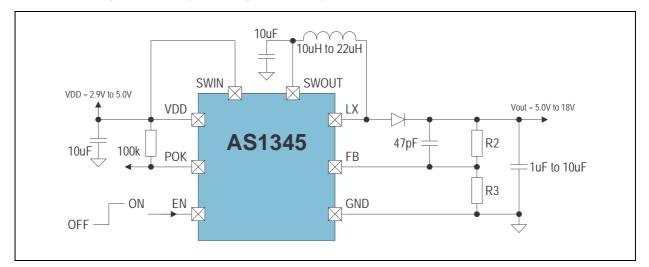




Figure AS1345 – 18:

AS1345 with Adjustable Output Voltage, without Output Disconnect

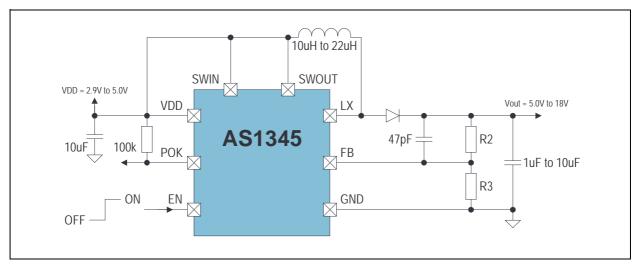


Figure AS1345 – 19: AS1345 with Fixed Output Voltage, with Output Disconnect

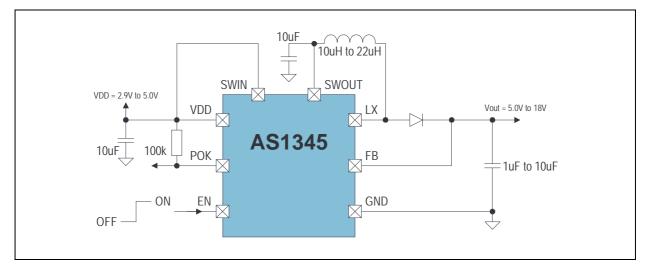
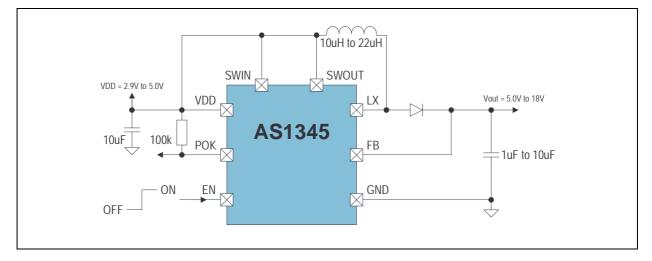


Figure AS1345 – 20:

AS1345 with Fixed Output Voltage, without Output Disconnect





Power OK Operation

If desired the POK functionality can be used. In this case a resistor R1 (~100k) has to be applied between the POK pin and VIN, because the POK output is an open drain type. If the POK functionality is not used the pin should be unconnected.

During shut-down the POK pin is high impedance to save current. Therefore it shows VIN if connected to VIN with a resistor or is floating otherwise. During start-up the POK goes to LOW. During normal operation it is usually HIGH but it goes to LOW if for some reason VOUT drops below 90% of the nominal output voltage.

Thermal Shutdown

To prevent the AS1345 from short-term misuse and overload conditions the chip includes a thermal overload protection. To block the normal operation mode all switches will be turned off. The device is in thermal shutdown when the junction temperature exceeds 150°C typ. To resume the normal operation the temperature has to drop below 140°C typ. A good thermal path should be provided to dissipate the heat generated within the package, especially at higher output power. To dissipate as much heat as possible from the package into a copper plane with as much area as possible, it's recommended to use multiple vias in the printed circuit board. It is recommended to solder the Exposed Pad to the GND plane.

Continuing operation in thermal overload conditions may damage the device, and therefore, is considered a bad practice.

Inductor Selection

For best efficiency, choose an inductor with high frequency core material, such as ferrite, to reduce core losses. The inductor should have low DCR (DC resistance) to reduce the I^2R losses, and must be able to handle the peak inductor current without saturating. A 10µH to 22µH inductor with greater than 500mA current rating and less than 500m Ω DCR is recommended. When smaller peak currents are selected, the inductor current specification can be reduced accordingly.



Figure AS1345 – 21: Recommended Inductors

Part Number	Value	Current	Resistance	Size (ins)	Supplier
ELJLA100KF	10µH	600mA	0.71Ω	1210	
ELJLA220KF	22µH	420mA	1.9Ω	1210	
ELJPA100KF2	10µH	400mA	0.35Ω	1210	
ELJPA220KF2	22µH	290mA	0.66Ω	1210	
ELJPA100KF	10µH	240mA	0.5Ω	1210	Panasonic www.panasonic.com
ELJPA150KF	15µH	220mA	0.74Ω	1210	
ELJPA220KF	22µH	185mA	1.15Ω	1210	
ELJPC100MF3	10µH	140mA	0.58Ω	1008	
ELJPC220MF3	22µH	100mA	1.22Ω	1008	
LQH32PN100MNO	10µH	750mA	0.38Ω	1210	
LQH32PN150MNO	15µH	600mA	0.57Ω	1210	
LQH32PN220MNO	22µH	500mA	0.81Ω	1210	
LQH3NPN100NGO	10µH	500mA	0.38Ω	1212	Murata
LQH3NPN150NGO	15µH	370mA	0.91Ω	1212	Manufacturing Company
LQH3NPN220NGO	22µH	340mA	1.1Ω	1212	www.murata.com
LQH2MCN100M52	10µH	200mA	2.27Ω	0806	
LQH2MCN150M52	15µH	150mA	3.5Ω	0806	
LQH2MCN220M52	22µH	130mA	5.5Ω	0806	

Capacitor Selection

The convertor requires three capacitors. Ceramic X5R or X7R types will minimize ESL and ESR while maintaining capacitance at rated voltage over temperature. The VIN capacitor should be 10μ F. The VOUT capacitor should be between 1μ F and 10μ F. A larger output capacitor should be used if lower peak to peak output voltage ripple is desired. A larger output capacitor will also improve load regulation on VOUT. See table below for a list of capacitors for input and output capacitor selection.



Figure AS1345 – 22: Recommended Capacitors

Part Number	Value	Voltage	TC Code	Size (ins)	Supplier
GRM31CR71E106KA12L	10µF	25V	Х7	1206	
GRM31CR71C106KAC7L	10µF	16V	Х7	1206	
GRM31CR71A106KA01L	10µF	10V	X7	1206	
GRM21BR70J106KE76L	10µF	6.3V	Х7	0805	Murata Manufacturing
GRM31CR71E475KA88L	4.7µF	25V	Х7	1206	Company www.murata.com
GRM21BR71C475KA73L	4.7µF	16V	Х7	0805	
GRM188R71E105KA12D	1µF	25V	Х7	0603	
GRM188R71C105KA12D	1µF	16V	Х7	0603	

Schottky Diode Selection

The selection of the external diode depends on the application. If IOUT is very low most of the time, and VOUT is high, select a diode with a low reverse current for best efficiency. For lower VOUT and higher IOUT, select a diode with a lower V_{FORWARD} and $R_{FORWARD}$.

Figure AS1345 – 23: Recommended Diodes

Part Number	Reverse Voltage	Average Rectified Current	Forward Voltage	Reverse Leakage Current	Package	Supplier	
MBR0540	40V	500mA	460mV @ 500mA	1µA @ 20V	SOD123	Fairchild Semiconductor www.fairchildsemi.com	
B140HW	40V	1000mA	460mV @ 500mA	0.35μA @ 20V	SOD123	Diodes Inc www.diodes.com	
PMEG2010AEB	20V	1A	200mV @ 500mA	320μA @ 20V	SOD523	NXP Semiconductors www.nxp.com	
CRS04	40V	1A	450mV @ 500mA	40μA @ 20V	3-2A1A (Toshiba)	Toshiba	
CRS06	20V	1A	325mV @ 500mA	250μA @ 20V	3-2A1A (Toshiba)	www.toshiba-components.com	

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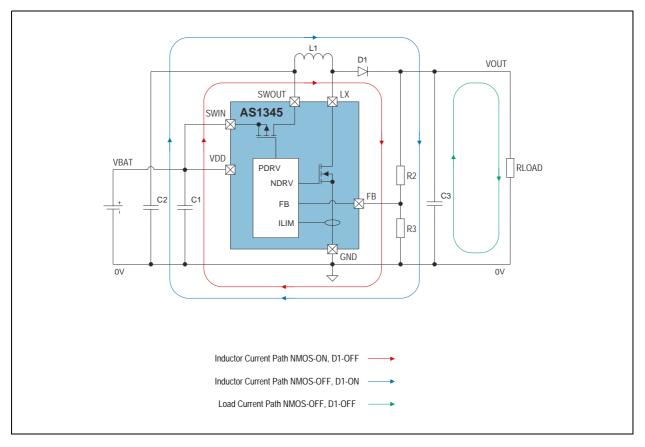
PCB Layout

Carefully printed circuit layout is important for minimizing ground bounce and noise. Keep the GND pin and ground pads for the input and output capacitors as close together as possible. Keep the connection to LX as short as possible. Locate the feedback resistors as close as possible to the FB pin and keep the feedback traces routed away from noisy areas such as LX.

EMI and overall performance quality are affected by the PCB layout. The high speed operation of the AS1345 demands careful attention to board layout. Stated performance will be difficult to achieve with careless layout. Figure 24 identifies the high current paths during an operation cycle involving the switching of the N-channel and P-channel internal switches. The current paths between SWIN, VIN, C1, C2, C4, L1, D1 and GND should be short and wide for lowest intrinsic resistive loss and lowest stray inductance.

A large ground pin copper area will help to lower the chip temperature. A multilayer board with a separate ground plane is ideal, but not absolutely necessary.

Figure AS1345 – 24: AS1345 - Inductor Current Paths

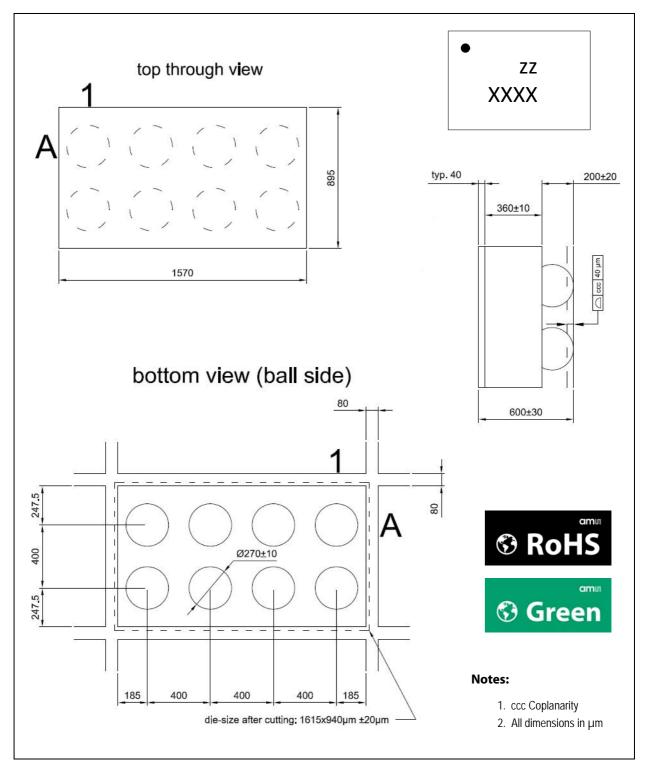




Package Drawings and Markings

The product is available in a 8-pin (2x2) TDFN and 8-bump (1.570mm x 0.895mm) WL-CSP package.

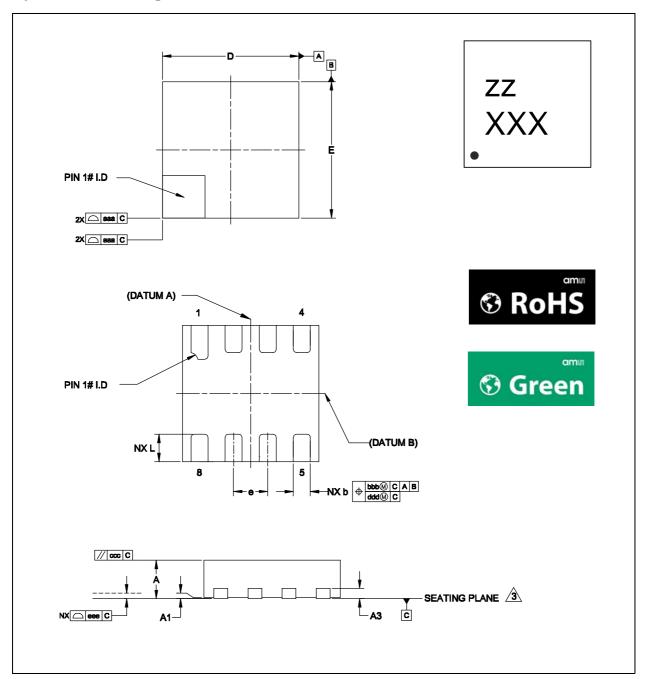
Figure AS1345 – 25: 8-bump WL-CSP with 0.4mm Pitch



Encoded Date Code	Marking Code
XXXX	ZZ



Figure AS1345 – 26: 8-pin (2x2) TDFN Package



Encoded Date Code	Marking Code	
XXX	ZZ	

Notes:

- 1. Dimensions & tolerancing conform to ASME Y14.5M-1994.
- 2. All dimensions are in millimeters. Angles are in degrees.
- 3. Coplanarity applies to the exposed heat slug as well as the terminal.
- 4. Radius on terminal is optional.
- 5. N is the total number of terminals.



Figure AS1345 – 27: Package Dimensions

Symbol	Min	Nom	Мах			
A	0.51	0.55	0.60			
A1	0.00	0.02	0.05			
A3	-	-	0.22			
L	0.45	0.55	0.65			
b	0.15	0.20	0.25			
D	2.00 BSC					
E	2.00 BSC					
e	0.50 BSC					
ааа	-	-				
bbb	-	0.10	-			
ссс	-	0.10	-			
ddd	-	0.05	-			
eee	-	0.08	-			
Ν	8					



Ordering Information

The device is available as the standard products listed in the table below.

On request, all devices can be factory set to enable a $100 k \Omega$ pull-down resistor for the EN pin.

Figure AS1345 – 28: Ordering Information

Ordering Code	Marking	I _{LIMIT}	Output	Description	Delivery Form	Package
AS1345A-BWLT-AD	BK	- 100mA	adjustable		Tape and up Reel	8-bumps (1.570x0.895m m) WL-CSP
AS1345A-BWLT-12	BS		12V			
AS1345A-BWLT-15	CA		15V			
AS1345A-BWLT-17	CI		17V			
AS1345A-BTDT-AD	BI	100mA	adjustable	18V, High Efficiency		
AS1345B-BTDT-AD	BJ	200mA	adjustable	DCDC Step-up Converter		8-pin (2x2mm) TDFN
AS1345C-BTDT-AD	CD	350mA	adjustable			
AS1345D-BTDT-AD	CL	500mA	adjustable			
AS1345D-BWLT-15	BG	500mA	15V			8-bumps (1.570x0.895m
AS1345D-BWLT-17	ВН	500mA	17V			m) WL-CSP

Notes:

- 1. All products are RoHS compliant and ams green.
- 2. Buy our products or get free samples online at <u>www.ams.com/ICdirect</u>
- 3. Technical Support is available at <u>www.ams.com/Technical-Support</u>
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